

#### **Description**

The HXY3400SI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

 $V_{DS} = 30V I_{D} = 6A$ 

 $R_{DS(ON)}$  < 28 m $\Omega$  @  $V_{GS}$ =10V

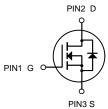
#### **Application**

Battery protection

Load switch

Uninterruptible power supply





N-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HXY3400SI	SOT-89	HD36	1000

### Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
Vos	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±12	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	6	А
ID@T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	4	А
Ідм	Pulsed Drain Current <sup>2</sup>	25.4	А
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	2.5	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θ</sub> JA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	92	°C/W



## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charac	cteristic		'		'	
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250µA	30	-	_	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V	-	-	±100	nA
On Charac	cteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	0.5	0.9	1.4	V
	Static Drain-Source on-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4.2A	-	20	28	mΩ
R <sub>DS(on)</sub>		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	25	34	
	TIONEZ	V <sub>GS</sub> =2.5V, I <sub>D</sub> =1A	-	35	50	
Dynamic C	Characteristics			•		
C <sub>iss</sub>	Input Capacitance	\\\\ 45\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	-	602	_	pF
Coss	Output Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V,	-	56	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	42	-	pF
Qg	Total Gate Charge	V <sub>DS</sub> =15V, I=4A,	-	4.8	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	1.2	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge	V <sub>GS</sub> =4.5V	-	1.7	-	nC
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-on Delay Time	)/ 45\/	-	12	_	ns
t <sub>r</sub>	Turn-on Rise Time	V <sub>DS</sub> =15V,	-	52	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	$I_D$ =4A, R <sub>GEN</sub> =3Ω, $V_{GS}$ =4.5V	-	17	-	ns
t <sub>f</sub>	Turn-off Fall Time	V <sub>GS</sub> -4.5V	-	10	-	ns
Drain-Sou	rce Diode Characteristics and Maxim	um Ratings				
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	7.0	А
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	25.2	Α
$V_{\text{SD}}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =5.8A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

<sup>2.</sup> Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



### **Typical Performance Characteristics**

Figure1: Output Characteristics

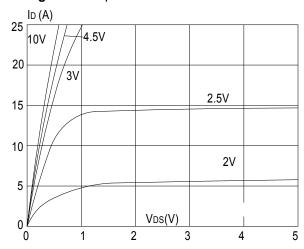


Figure 2: Typical Transfer Characteristics

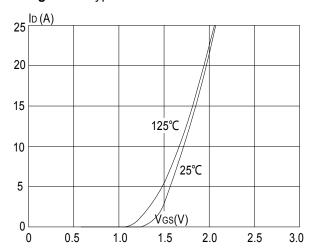


Figure 3:On-resistance vs. Drain Current

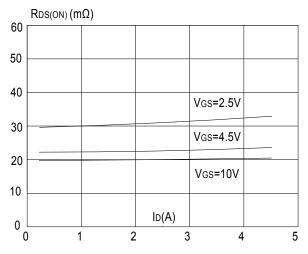


Figure 4: Body Diode Characteristics

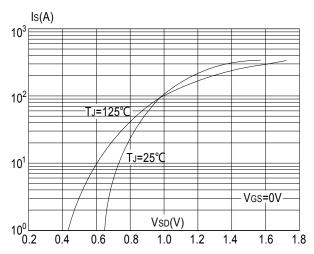


Figure 5: Gate Charge Characteristics

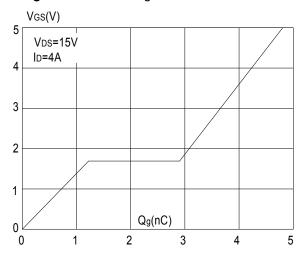
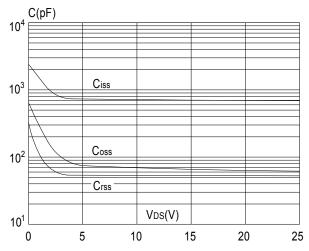


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

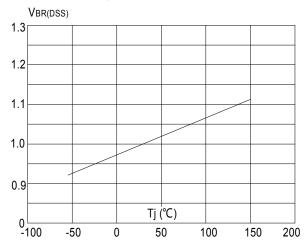
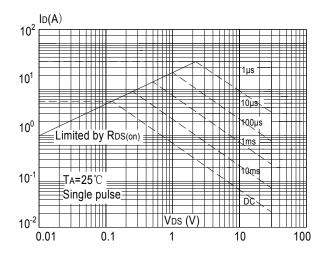
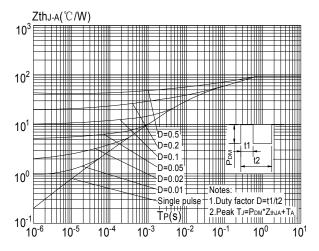


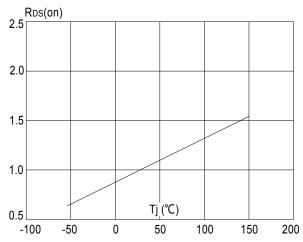
Figure 9: Maximum Safe Operating Area



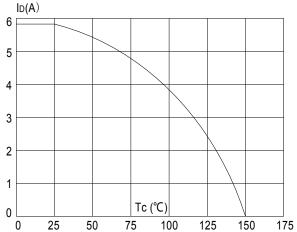
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



**Figure 8:** Normalized on Resistance vs. Junction Temperature

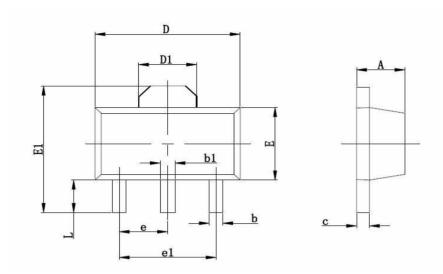


**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature





# **SOT-89 Package Outline Dimensions**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
Α	1.400	1.600	0.055	0.063
b	0.350	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
С	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.350	2.550	0.091	0.102
E1	3.940	4.250	0.155	0.167
е	1.500 TYP		0.060TYP	
e1	3.000 TYP		0.118TYP	
L	0.900	1.100	0.035	0.047

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